

Formation of an order in a system of exciton condensed phase islands in quantum wells

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A theory of exciton condensed phase creation in two-dimensional system is presented. The theory is applied to explain the appearance of the periodical fragmentation which was observed last years in luminescence from the ring around laser spot in crystal with double quantum wells.

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An electrons and holes of indirect excitons in semiconductor coupled quantum wells are localized in different wells and as the result the excitons have long lifetime. Such system present interest for study of exciton condensation phenomena [1]. Recently interesting experiments were fulfilled for indirect excitons in AlGaAs and InGaAs crystals with coupled quantum wells. In works [2, 3, 4, 5, 6, 7] the authors have observed a ring structure in emission of indirect excitons outside of laser spot. The distance between ring and center of the excitation spot grows with increasing the pumping and can reach several hundred microns that is much larger than the exciton diffusion length. At low temperature ($T \approx 2K$) the external ring is fragmented into periodical structure over macroscopic lengths. The mechanism of the luminescence ring formation was proposed in [6, 7]. The origin of fragmentation along the ring is unclear. In present work the appearance of this fragmentation is explained by creation of islands of exciton condensed phases along the ring. In [8, 9] it was shown that in the presence of an attractive interaction between excitons a high density exciton system is unstable with respect to the periodical structure appearance. To obtain the spacial dependence of the exciton generation rate we shall use the suggestion of paper [6, 7] that in absence of the light irradiation the quantum well contains electrons and that holes created by light are captured by quantum well more

effectively than electrons. As the result the charge separation takes place from positive charge value in the center of laser spot till negative one far from the spot. The emission of light occurs from a ring where product of the electron and hole densities has maximum. For determination of the density distribution we have used the system of equations similar to that investigated in [6, 7] but we added the equation for the exciton density. Lets $n_e; n_h; n_{ex}$ designate the well densities of electrons, holes and excitons, respectively. These values satisfy to the following kinetic equations

$$\frac{\partial n_e}{\partial t} = D_e \nabla^2 n_e + K_e(r) - W n_e n_h - \frac{n_e - n_0}{\tau_e}; \quad (1)$$

$$\frac{\partial n_h}{\partial t} = D_h \nabla^2 n_h + K_h(r) - W n_e n_h - \frac{n_h}{\tau_h}; \quad (2)$$

$$\frac{\partial n_{ex}}{\partial t} = D_{ex} \nabla^2 n_{ex} + G - \frac{n_{ex}}{\tau_{ex}}; \quad (3)$$

where D_e, D_h and D_{ex} are the diffusion coefficients, τ_e, τ_h and τ_{ex} are the lifetime for electrons, holes and excitons, respectively, W is the electron-hole recombination rate, $K_e (K_h)$ is the electron (hole) creation rate in the well, G is the exciton production rate ($G = qW n_e n_h; q \ll 1$).

Fig.1 shows the result of calculations of electron, hole and exciton densities for the following values of parameters: $D_e = 200 \text{ cm}^2/\text{s}, D_h = 50 \text{ cm}^2/\text{s}, D_{ex} = 10 \text{ cm}^2/\text{s}, W = 150 \text{ cm}^2/\text{s}, q = 0.9, \tau_e = \tau_h = 10^{-5} \text{ s}, \tau_{ex} = 10^{-7} \text{ s}$, the spacial distribution of the pumping was approximated by the Gaussian curve with width 60 nm and $K_h = 2K_e$. The qualitative picture of behavior of $n_e; n_h$ as a function of r is similar to results obtained in [6, 7]. The position of the exciton density maximum determines the ring luminescence in experiments. We shall use the obtained value of exciton density to study the fragmentation of the exciton condensed phase. It is suggested that the condensation occurs due to the exciton-exciton interaction and it is not the Bose-Einstein condensation in the wave vector space with $k = 0$. We have estimated the Van der Waals attraction using the well known formula of quantum mechanics and showed that Van der Waals interaction between two indirect excitons in coupled quantum wells exceeds the dipole-dipole interactions in the range of distances between excitons of order of several exciton radiuses (See Appendix). The attractive interaction may cause the existence of the exciton condensed phase. Some models of phase transitions in a system of indirect excitons were studied in [10]. Afterwards we shall suggest that condensed phase exists and it is described by some parameters which will be determined later. Due to a finite value of the exciton

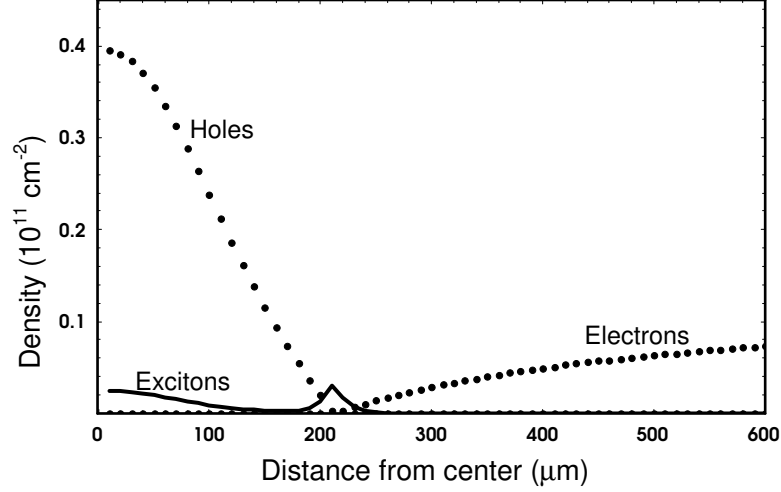


Figure 1: The dependence of electron, hole and exciton densities on distance from center

lifetime the sizes of exciton condensed phases are restricted. As the result in the two-dimensional case the condensed phase must exist as a system of islands similar to electron-hole drops in bulk semiconductors. In studied system the islands should be localized on the ring where the exciton density has maximum.

Under following consideration we shall apply the theory of creation of the exciton condensed phase islands in two-dimensional case [11] to studied system with nonuniform pumping. Firstly, we shall study the system of condensed phase islands periodically situated along the ring at maximum of the exciton density with $r = r_0$ (Fig 2). $\varphi_m = 2\pi m/N$ is the angle of m -th island on the ring. Afterwards we shall show that deviations (fluctuations) from periodicity are small. Let us consider the formation of some island, for example, the island with $m = 0$. We introduce the distribution function f_n , which determines a probability of the island with $m = 0$ to have n excitons. The size of disks is determined by four processes: creation of excitons by pumping, capture of the excitons from environment, escape of excitons from the disk, and the exciton decay. The kinetic equation for the distribution function have the following form

$$\frac{\partial f_n}{\partial t} = j_{n+1} + j_n; \quad (4)$$

where j_n is the probability current

$$j_n = 2R_{n-1}W_{fi}(R_{n-1})c(R_{n-1})f_{n-1} - 2R_nW_{if}(R_n)c_1f_n - R_n^2f_n =_{ex} + R_{n-1}^2G_{n-1}f_{n-1}; \quad (5)$$

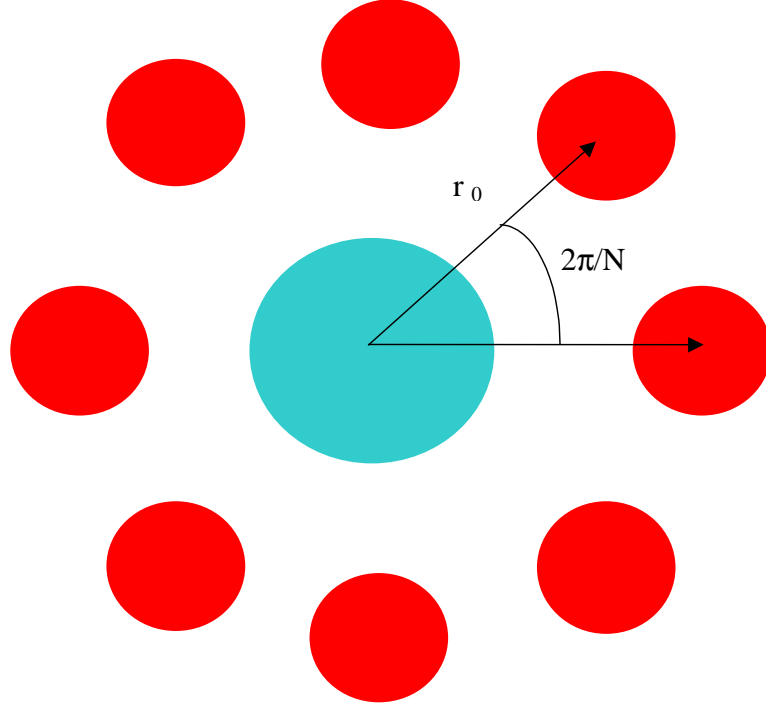


Figure 2: The position of exciton condensed phase islands around the laser excitation spot

R_n is the radius of the disk with n excitons, $W_{fi}(R_n)$ and $W_{if}(R_n)$ are probabilities for the exciton to be captured by the disk and to escape from the disk per unit length of the circle, respectively, $G_n = \int_0^{R_n} G(r) dS_n = R_n^2$ is the mean value of the exciton pumping over island area, $c(R_n)$ and c_i are the concentrations of excitons on the circle of the disk and inside disk ($c_i = 1/s_0$, s_0 is the area per single electron-hole pair in the island). The exciton concentration $c(r)$ differs from $n_{ex}(r)$ presented in Fig.1 due to presence of islands which perturb the exciton concentration field around them. The following condition between transition probabilities W_{fi} and W_{if} takes place due to the detail balance principle

$$\frac{W_{if}(R)}{W_{fi}(R)} = \frac{W_{if}(l)}{W_{fi}(l)} \exp \left(-\frac{a_2}{R} \right); \quad (6)$$

where $W_{fi}(l)$ and $W_{if}(l)$ are the transition probabilities in the case of straight line boundary between condensed and gas phases, $W_{fi}(l) = W_{if}(l) = c_i = c_1$, c_1 is the equilibrium concentration of excitons for the straight line boundary between condensed and gas phases

$$c_1 = c_{10} \exp(-\epsilon/T); \quad (7)$$

ϵ is the condensation energy per an exciton, $c_{10} = (\mu - T = 2 \hbar^2 / m)$ is the effective exciton mass, μ is the degeneracy of the exciton state, $a_2 = a_1 s_0 = T$, a_1 is the energy per unit of the disk length.

The connection between islands occurs due to dependence of the exciton surface concentration of considered island $c(R_n)$ in the kinetic equation (4) versus presence of other islands. We suggest that the distance between disks is larger than the disk radius and the concentration field created by some island slowly changes in limits of a size of the considered island. As the result the exciton concentration on the disk with $m = 0$ may be presented in the form

$$c_{ex}(R) = n_{ex}(r_0) + a_0 K_0((R=l) + \sum_{i=0}^N K_0(2r_0 \sin(\theta/2)=l)); \quad (8)$$

where $K_0(x)$ is the modified Bessel function, l is the diffusion length of free exciton. Coefficients a are determined by boundary conditions on every disk: the current of excitons to an island should be equal difference between number of excitons captured by the island and the number of excitons which escape from the island

$$2 \pi R D_{ex} \frac{\partial c_{ex}(R)}{\partial R} = 2 \pi R (W_{fi} c_{ex}(R) - W_{if} c_i); \quad (9)$$

Due to the system symmetry all islands have equal parameters: $a_i = a_0$ for every i . Further we introduce the radius distribution function $f(R) = f_n dn = dR = 2 \pi R f_n = s_0$. In steady case at $n \gg 1$ the solution of the equation (4) has the form

$$f(R; N) = f_0 \exp(-F(R; N)); \quad (10)$$

where

$$F(R; N) = 4 \int_0^R \frac{n_{ex}(r_0) + c_{10} e^{-\frac{(r-a=R)}{T}}}{n_{ex}(r_0) + c_{10} e^{-\frac{(r-a=R)}{T}}} \frac{R' - 1 + n_G + \frac{(K_0(R'=1) + (N))}{K_1(R'=1)}}{R' - 1 + n_G + \frac{(K_0(R'=1) + (N))}{K_1(R'=1)}} R' dR'; \quad (11)$$

$$(N) = \sum_{i=1}^{N-1} K_0(2r_0 \sin(\theta/2)=l); \quad (12)$$

Here we have introduced the dimensionless variables $R' = R / \overline{s_0}$; $c(R') = c(R) / s_0$; $n_G = W_{fi} / \overline{s_0}$; $n_G = G s_{0, ex}$, ϵ and a are expressed in (10) and (11) in units of temperature. The most probable radius is determined from the condition

$$\frac{\partial F(R; N)}{\partial R} = 0; \quad (13)$$

The mean radius depends on the number of islands is $R = R(N)$. The probability for system to have N islands with radiuses $R_1; R_2; \dots; R_N$ equals to

$$W(N; R_1; R_2; \dots; R_N) = \exp\left(-\sum_i F(R_i; N)\right); \quad (14)$$

After integrating over the radiuses of the disks we obtain the probability for the system to have N islands on the ring

$$W(N) = \exp(-\langle N \rangle); \quad (15)$$

where

$$\langle N \rangle = -N \ln z(N); z(N) = \int_0^{z_1} \exp(-F(R(N); N)) dR; \quad (16)$$

The number of islands is determined by the condition

$$\frac{\partial}{\partial N} = 0; \quad (17)$$

The formulae (13, 17) determine the mean radius and number of islands. Since islands of condensed phases derive excitons from the same source two islands can not be situated close one to another. Moreover, the distance between islands can not be large because in this case the exciton density between them becomes greater than critical value and as the result the new island may appear. So, there is specific interaction between condensed phases through the exciton concentration fields. As the result the dependence $\langle N \rangle$ (17) has minimum at some value $N = N_s$ that determines the number of islands on the ring. We have calculated the some parameters of the islands on the ring using the equations (10-17). The exciton parameters and parameters of pumping are the same as parameters in Fig.1. The following parameters of the condensed phase were chosen: $m = 0.37m_0$; $\tau = 10\text{K}$; $a_2 = 18\text{K}$; $s_0 = 10^{11} \text{ cm}^{-2}$. It is seen from Fig.3 that the distance between islands ($d = 2r_0 = N_s$) increases with rise of temperature, the island radius changes slowly with temperature. At considered parameters the condensed phase exists till 2.16K .

To estimate the island position fluctuation we studied the shift of some island versus the angle ϕ along the ring at fixed position of all other islands (similar to Einstein model for crystal oscillations). In this case the function $\langle N \rangle$ in (13) depends on ϕ ($\langle N \rangle = \langle N; \phi \rangle$) and the function $f(R; N) = f(R; N; \phi)$ determines the angle distribution function. Using it we calculated the mean fluctuation

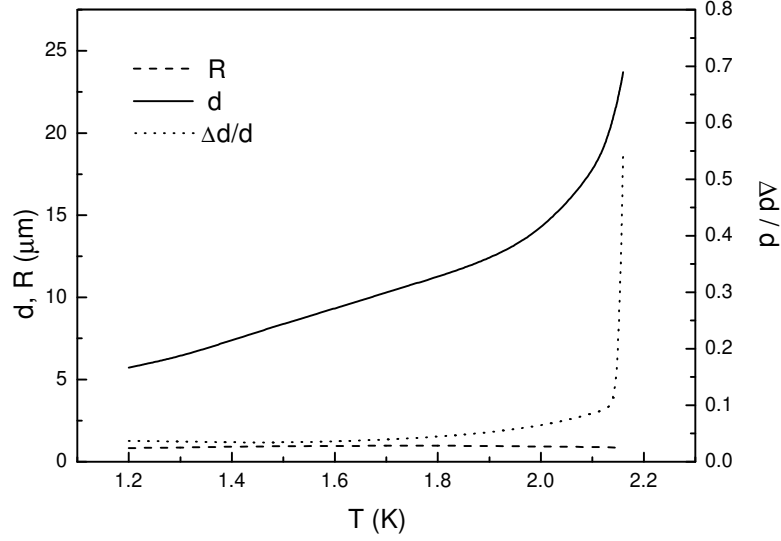


Figure 3: The dependence of the island radius (R), the distance between islands (d) and the ratio of island fluctuation shift to distance between islands ($\Delta d/d$) on temperature

shift of island along the ring, which equals $\Delta d = r_0 \frac{q}{r^2}$. It is seen from Fig.3 that the relative shift $\Delta d/d$ is small ($\Delta d/d \ll 1$) and increases only in the vicinity of temperature at which the condensed phase disappears. By similar way using (15) the relative fluctuations of the island number ($\Delta N/N_s = \frac{q}{(N - N_s)^2} N_s$) were calculated. This value is much less than unity. For example, we have $\Delta N/N_s = 7 \cdot 10^3$ at $T = 2K$. Thus, the studied system has perfect periodicity. These results explain the periodical fragmentation observed in [2].

We suggested that outside of islands the exciton gas is nongenerated. At considered parameters the exciton density at the surface of disks outside of disks equals to $7.2 \cdot 10^{10} \text{ cm}^{-2}$ and is significantly lower than the critical Bose-Einstein condensation density. Inside of islands the exciton density is significantly higher and taking into account the Bose statistic may be important. But presented theory did not consider the model of the condensed phase and needs only some parameters of the condensed phase: energy and occupied volume per electron-hole pair and surface energy. Moreover, the condensed phase may present electron-hole liquid phase.

In the paper the binding energy per electron-hole pair in condensed phase was chosen ($\epsilon' = 10K = 0.8 \text{ meV}$). This value gives the critical temperature of fragmentation disappearance ($2.16K$) close to experimental meaning ($2K$). The value of ϵ' is less than width of the fragment emission

line (1.3m eV [2]) and the emission line spectral positions of free exciton and the fragment coincide practically. Even there is very small (much less than width) shift of the fragment emission to blue side (See Fig2c of [2]). But mechanisms, that determine the width (scattering by fluctuation potential, phonons, between excitons and others), give different contribution to the shapes of emission spectra (including to the shift of lines) for the free excitons and the exciton condensed phase. So, if the exciton binding energy to condensed phase is less than the bandwidth, the physical information from comparison of emission spectra shapes of free excitons and the condensed phase can be obtained only together with analysis of line broadening mechanisms for these states. For that the detailed theory of the condensed phase is needed.

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Appendix

To estimate the Van der Waals interaction between two excitons let us use the well known formula

$$U_{vdw} = \sum_{i_1 \neq 0; i_2 \neq 0} \frac{\langle 0;0 | U_{dd} | i_1; i_2 \rangle \langle i_1; i_2 | U_{dd} | 0;0 \rangle}{E_{i_1; i_2} E_{0;0}}, \quad (18)$$

where $U_{dd} = \frac{P_1 P_2}{R_{12}^3} - \frac{3P_1 R_{12} P_2 R_{12}}{R_{12}^5}$ is the operator of the dipole-dipole interaction between excitons, R_{12} is the distance between excitons, $|0;0\rangle$ and $|i_1; i_2\rangle$ are the ground and excited states of a system with two excitons. The formula U_{dd} can be used if the distance between excitons is larger than exciton radius. For calculation we have used the following model. Electron and hole are localized in different wells. The distance between wells is equal to a . For estimation we took into account only the ground state and two lowest excited states, the dipole transition matrix element of which from ground state to excited one does not equal to zero. The wave functions of such type have the form

$$|j_0\rangle = A_0 \exp(-\alpha_0 r); |j_{1a}\rangle = A_{1a} r \cos' \exp(-\alpha_{1a} r); |j_{1b}\rangle = A_{1b} r \sin' \exp(-\alpha_{1b} r); \quad (19)$$

r is the distance between electron and hole in exciton in the plane of wells, $\alpha_0; \alpha_{1a}; \alpha_{1b}$ are variational parameters. The results of calculation of the dipole-dipole and Van der Waals interaction ($\langle 0;0 | U_{dd} | j_0 \rangle + U_{vdw}$) are presented in Fig.4 for different values of a . The energy of bulk exciton

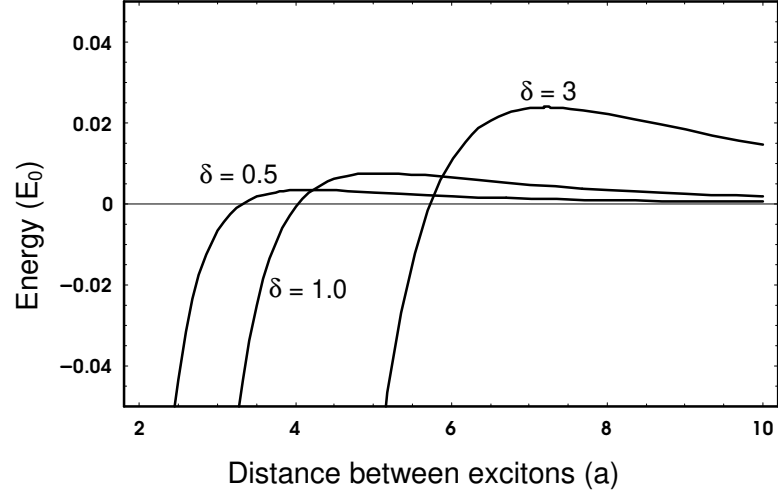


Figure 4: The dependence of the sum of the Van der Waals and dipole-dipole interaction energies between two excitons in coupled quantum wells on the distance between excitons for the different values of the distance between wells δ . E_0 and a are the energy and radius of exciton, respectively, in bulk crystal

is chosen as a unit of energy, radius of bulk exciton (the value of order of 50 \AA) is the unit of length. At the large distance the interaction between excitons is dipole-dipole repulsive. But the attractive Van der Waals interaction exceeds the dipole-dipole repulsion at distances less than $3 - 6$ exciton radii and total interaction is attractive. The taking into account the other more highly excited intermediate states in (18) should lead to increasing the presented estimations of Van der Waals interaction. So, Van der Waals interaction is really larger. At small distances between excitons the exchange interaction becomes important, also the approximation of dipole-dipole interaction becomes inapplicable. As the result the total interaction is repulsive one at small distances.

It should be noted that attractive interaction may be significant at low temperature when condensed phase is created. At higher temperature excitons are distributed uniformly over crystal, the mean distance between excitons exceeds the region of attraction and main contribution to the exciton-exciton interaction gives the dipole-dipole one.

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